

Prof. Ohmi's Paper

January—December, 1988

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- 9(C) T. Ohmi, S. Yoshitake, J. Murota, T. Okumura, and H. Aikawa, "High Quality Epitaxial Silicon Layers Formed by Ultra Clean Technology," Extended Abstracts, 173rd Electrochemical Society Spring Meeting, Atlanta, Abstract No. 189, pp. 294-295, Vol. 88-1, May 1988.
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- 11(C) T. Ohmi, M. Morita, and T. Hattori, "Defects and Impurities in SiO₂ Interface for Oxides Prepared Using Superclean Methods," Extended Abstracts, 173th Electrochemical Society Spring Meeting, Atlanta, Abstract No. 256, pp. 387-388, May 1988.
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- 12(C) T. Ohmi, T. Saito, T. Shibata, and T. Nitta, "Copper ULSI Metallization by Low Kinetic-energy Particle Process," Digest of Technical Papers, 1988 Symposium on VLSI Technology, San Diego, pp. 99-100, May 1988.
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